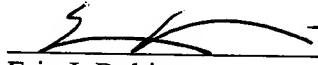


REMARKS

The specification has been corrected in accordance with 37 CFR §1.121.

Examination on the merits is requested.

Respectfully submitted,



Eric J. Robinson  
Registration No. 38,285

NIXON PEABODY LLP  
8180 Greensboro Drive, Suite 800  
McLean, Virginia 22102  
(703) 790-9110

098005-072701

VERSION WITH MARKINGS TO SHOW CHANGES MADE

Please replace page 13, paragraph 3 as follows:

However, in the first embodiment, niobium oxide is used for the high-refractive-index film 13b of the end facet reflective film 13, and the light absorption coefficient of niobium oxide is lower than that of titanium oxide. Thus, a rise in temperature in the vicinity of the end facet of the resonant cavity 13 [12] can be suppressed. As a result, the crystallinity of the quantum well active layer 1 and the surrounding portions thereof is less likely to deteriorate, and the semiconductor laser device can increase its output power. The active layer has a quantum well structure in the illustrated embodiment but does not have to do so.

Please replace page 21, last paragraph as follows:

In addition, a Group III-V nitride semiconductor, containing gallium nitride as a main component, is used as a semiconductor material for the violet-light-emitting semiconductor laser device with an oscillation wavelength of about 400 nm. Alternatively, any of Group [II-IV] II-VI compound semiconductors such as zinc selenide (ZnSe), zinc sulfide (ZnS) and zinc oxide (Zno) may also be used.

09890095-072701